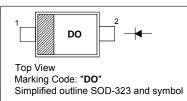
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- Super-high speed switching circuit
- · Small current rectification

PINNING

PIN	DESCRIPTION	
1	Cathode	
2	Anode	



Absolute Maximum Ratings ($T_a = 25 \, ^{\circ}$ C)

Parameter	Symbol	Value	Unit	
Reverse Voltage	V _R	30	V	
Peak Forward Current	I _{FM}	300	mA	
Average Forward Current	I _{F(AV)}	200	mA	
Non-repetitive Peak Forward Surge Current 1)	I _{FSM}	1	Α	
Junction Temperature	TJ	150	°C	
Storage Temperature Range	T _s	- 55 to + 150	°C	

¹⁾ The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

Characteristics at T_a = 25 °C

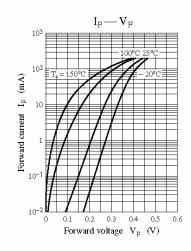
Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	-	0.55	V
Reverse Current at V _R = 30 V	I _R	-	50	μΑ
Terminal Capacitance at f = 1 MHz	Ст	30	-	pF
Reverse Recovery Time at $I_F = I_R = 100$ mA, $I_{rr} = 10$ mA, $R_{L=} = 100$ Ω	t _{rr}	3	-	ns

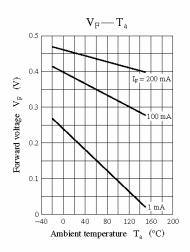


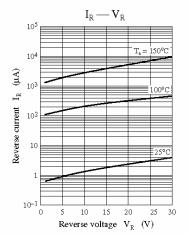


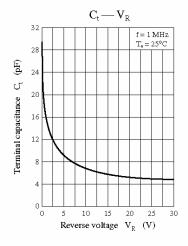


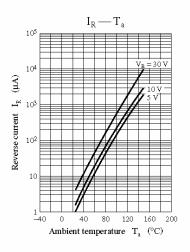
SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



















USO/TS 16949 : 2002 ISO 14001 : 2004 ISO 9001 : 2000 Certificate No. 05103 Certificate No. 7116 Certificate No. 0506098

SEMTECH ELECTRONICS LTD.

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

